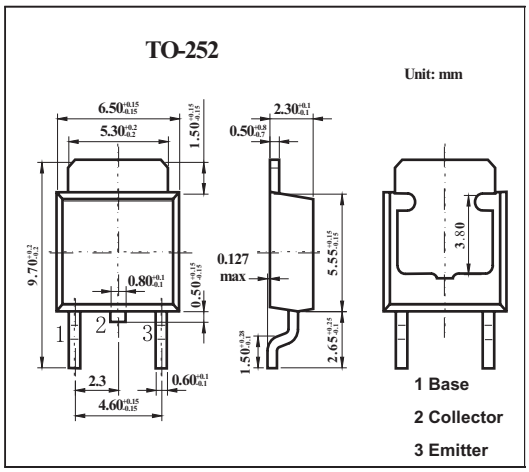
Silicon NPN Triple Diffused Type

2SC5356



■ Features

- Excellent switching times: t_f = 0.5 μs (max) (I_C = 1.2 A)
- High collectors breakdown voltage: V_{CEO} = 800 V
- High DC current gain: h_{FE} = 15 (min) (I_C = 0.15 A)

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	900	V
Collector-emitter voltage	V_{CEO}	800	V
Emitter-base voltage	V_{EBO}	7	V
Collector current (DC)	I_C	3	A
Collector current (Pulse)	I_{CP}	5	
Base current	I_B	1	A
Collector power dissipation Ta = 25℃	P_C	1.5	W
Tc = 25℃		25	
Junction temperature	T_j	150	℃
Storage temperature range	T_{stg}	-55 to +150	℃

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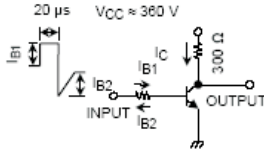
■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cut-off current	I_{CBO}	V_{CB} = 720 V, I_E = 0			100	μA
Emitter cut-off current	I_{EBO}	V_{EB} = 7 V, I_C = 0			10	μA
Collector-base breakdown voltage	$V_{(BR)\ CBO}$	I_C = 1 mA, I_E = 0	900			V
Collector-emitter breakdown voltage	$V_{(BR)\ CEO}$	I_C = 10 mA, I_B = 0	800			V
DC current gain	h_{FE}	V_{CE} = 5 V, I_C = 1 mA	10			
		V_{CE} = 5 V, I_C = 0.15 A	15			
Collector-emitter saturation voltage	$V_{CE\ (sat)}$	I_C = 1.2 A, I_B = 0.24 A			1.0	V
Base-emitter saturation voltage	$V_{BE\ (sat)}$	I_C = 2 A, I_B = 0.24 A			1.3	V
Switching time Rise time	t_r				0.7	μs
Switching time Storage time	t_{stg}				4.0	
Switching time Fall time	t_f	I_{B1} = 0.24 A, I_{B2} = −0.48 A DUTY CYCLE ≤ 1%			0.5	

■ Marking

Marking	C5356